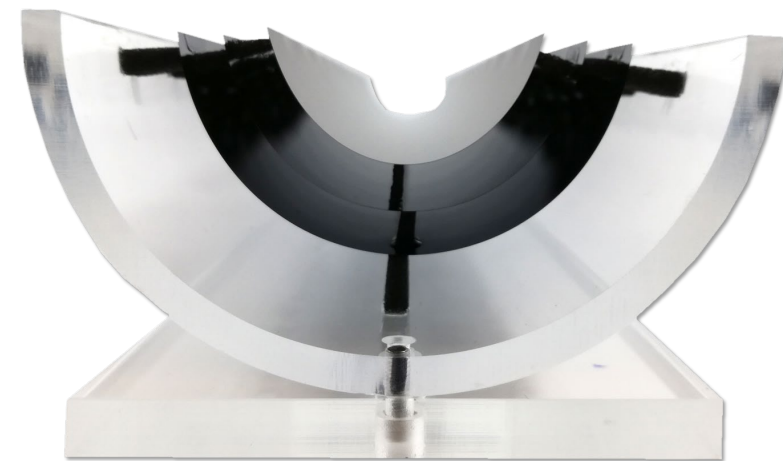


ALICE ITS3 WP3-4-5 Progress report

Giacomo Contin

Università di Trieste and INFN Sezione di Trieste

EIC Silicon Consortium meeting – May 17th 2021



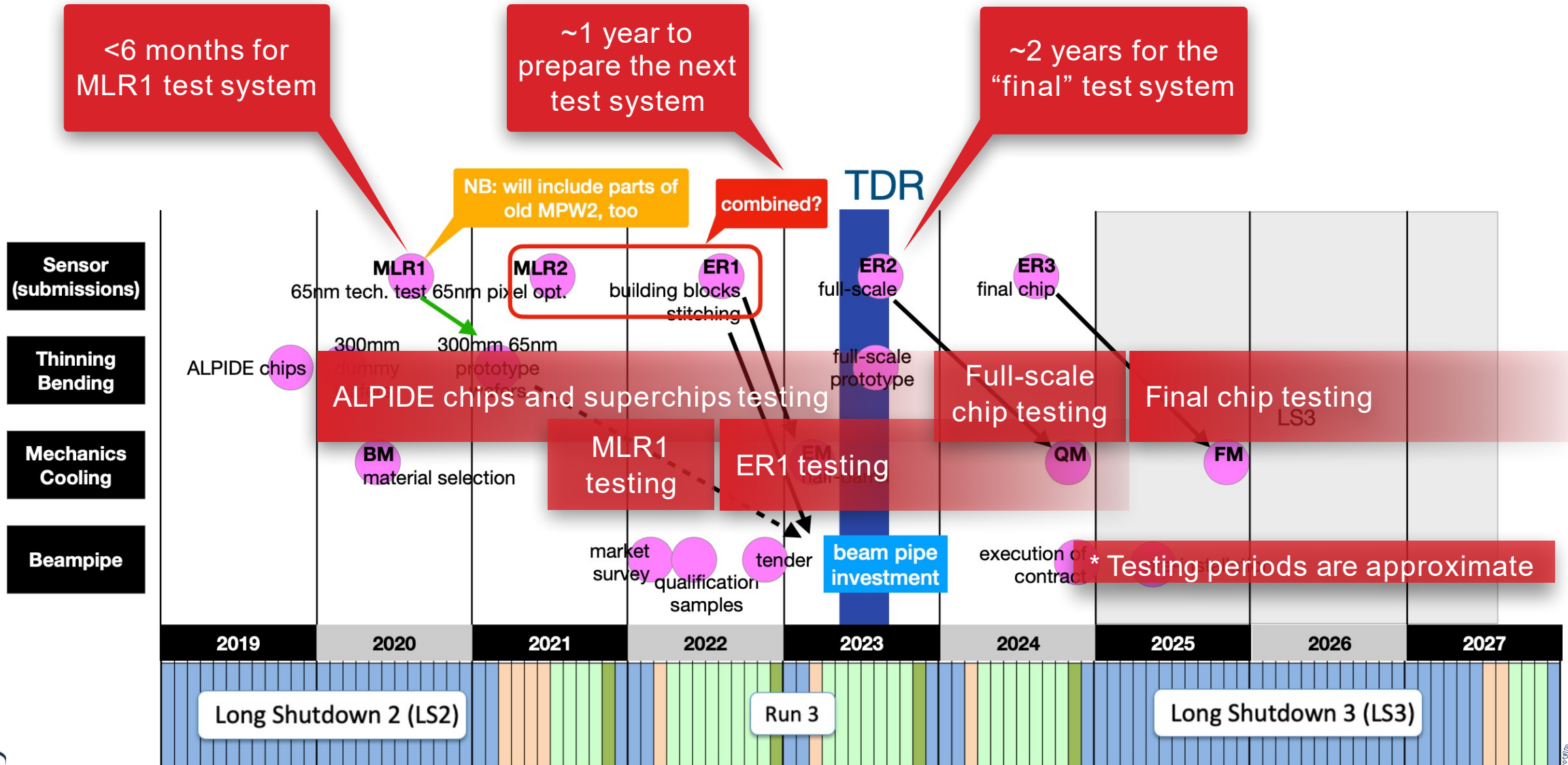
Summary



- MLR1 Testing campaign plans
- ALPIDE-based DUT Testbeams
- Larger-size chip Thinning, Bending and Interconnections
- Mechanics development



ITS3 project timeline: testing



Testing of MLR1 pixel matrices

From June and for ~1 year

- ▶ Short time to prepare the test system and short usage time → avoid custom solutions
- ▶ Provide feedback for ER1 quickly → distribute the characterisation workload
- ▶ **Solutions:** several “carrier cards” + “proximity board”
 - Existing test system, or
 - General purpose components (oscilloscopes, dev boards...)
- ▶ **To keep in mind:**
 - Testbeams, bending tests, irradiation, yield...
 - >100 chips on “carrier card”/“proximity boards” & ~20 test systems

X 4 (APTS, DPTS, CE65, CA)

Testing plan & timeline summary

Miko Suljic @ ITS3 Plenary 23.04.2021

- ▶ T_0 (June) = delivery of first batch of chips on carriers to testing sites participating in carrier design, software or firmware development
- ▶ $T_0 + 3$ weeks (early July) = decision on the next batch of chips to be bonded and distributed to all testing sites
- ▶ $T_0 + 7$ weeks (early August) = decision on the chip variants to be bonded and irradiated (TID) or bonded after irradiation (NIEL), bonded for further exploration of parameter phase space (APTS)

Testbeam slots:

- ▶ mid-Jul @ SPS
- ▶ end-Oct @ PS
- ▶ beg-Nov @ SPS

Chip testing phase space

Miko Suljic @ ITS3 Plenary 23.04.2021

APTS

#	Pitch (um)	Buffer	Coupling	Process	#	Pitch (um)	Buffer	Coupling	Process
1	10	SF	DC	std	19	10	SF+amp	DC	std
2	10	SF	DC	mod	20	10	SF+amp	DC	mod
3	10	SF	DC	gap	21	10	SF+amp	DC	gap
4	15	SF	DC	std	22	20	SF+amp	DC	std
5	15	SF	DC	mod	23	20	SF+amp	DC	mod
6	15	SF	DC	gap	24	20	SF+amp	DC	gap
7	20	SF	DC	std	25	10	SF+amp	AC	std
8	20	SF	DC	mod	26	10	SF+amp	AC	mod
9	20	SF	DC	gap	27	10	SF+amp	AC	gap
10	25	SF	DC	std	28	20	SF+amp	AC	std
11	25	SF	DC	mod	29	20	SF+amp	AC	mod
12	25	SF	DC	gap	30	20	SF+amp	AC	gap
13	10	SF	AC	std	31	10	OPAMP	DC	std
14	10	SF	AC	mod	32	10	OPAMP	DC	mod
15	10	SF	AC	gap	33	10	OPAMP	DC	gap
16	20	SF	AC	std	34	10	OPAMP	AC	std
17	20	SF	AC	mod	35	10	OPAMP	AC	mod
18	20	SF	AC	gap	36	10	OPAMP	AC	gap
					37	10	SF mux	DC	gap
					38	20	SF mux	DC	gap

CE65

#	Pitch (um)	Buffer [coupling]	Process
A	15	Amp [AC], Amp [DC], SF [DC]	std
B	15	Amp [AC], Amp [DC], SF [DC]	gap
C	15	Amp [AC], Amp [DC], SF [DC]	Mod
D	25	Amp [AC], Amp [DC], SF [DC]	std

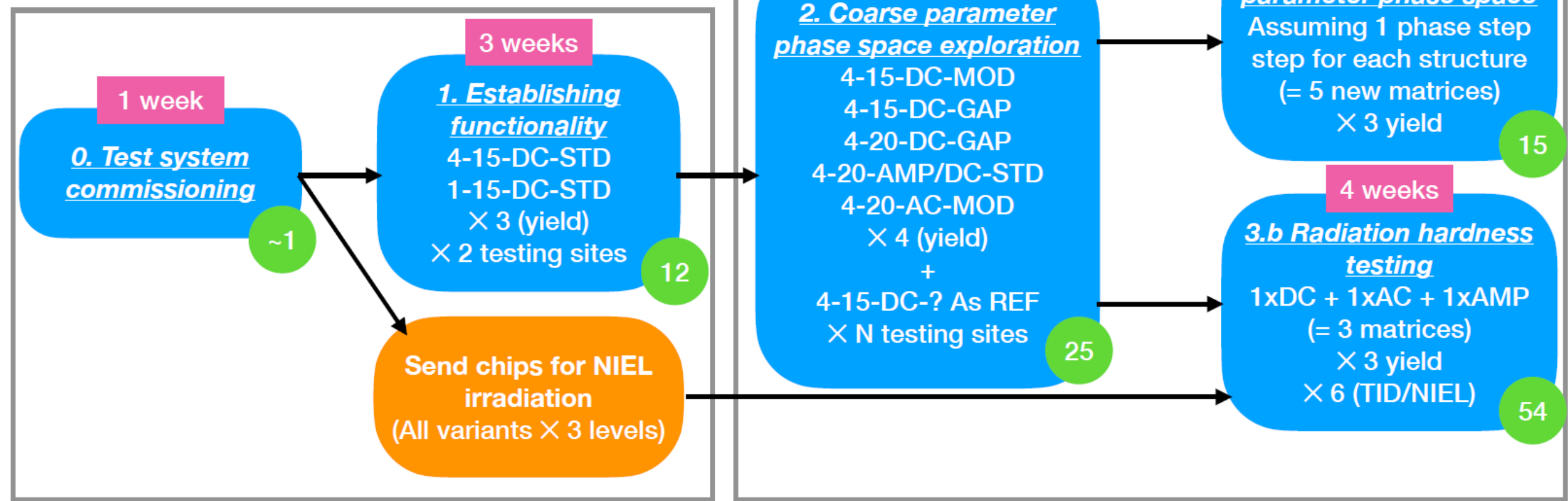
DPTS

#	Pitch (um)	Variant
1	15	Base
2	15	Column cross connect
3	15	column cross connect, shorted DVSS AVSS

To test on splits 1 & 4

To test on split 4

APTS SF (Low sampling rate)



1st carrier production (~15)

2nd carrier production (~100)

1st bonding (~12)

2nd bonding (~25)

3rd bonding (~70)

N carrier + spares!
Time to provide first feedback

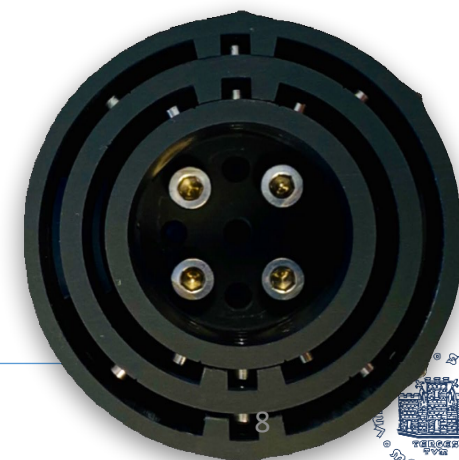
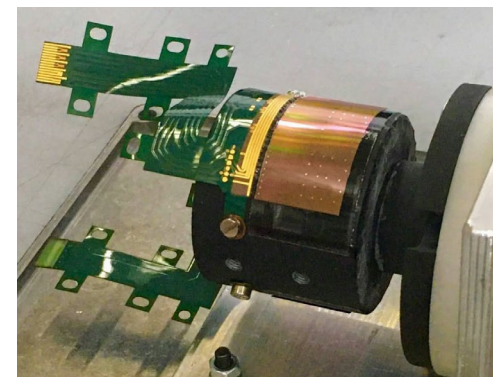
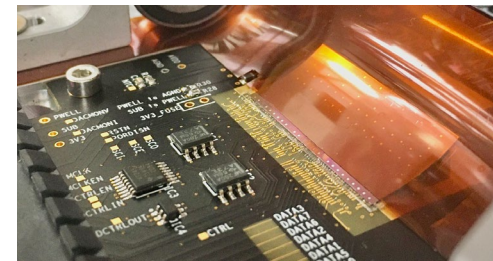
TBD:
testing sites

Miko Suljic @ ITS3 Plenary 23.04.2021

Bent ALPIDE testing

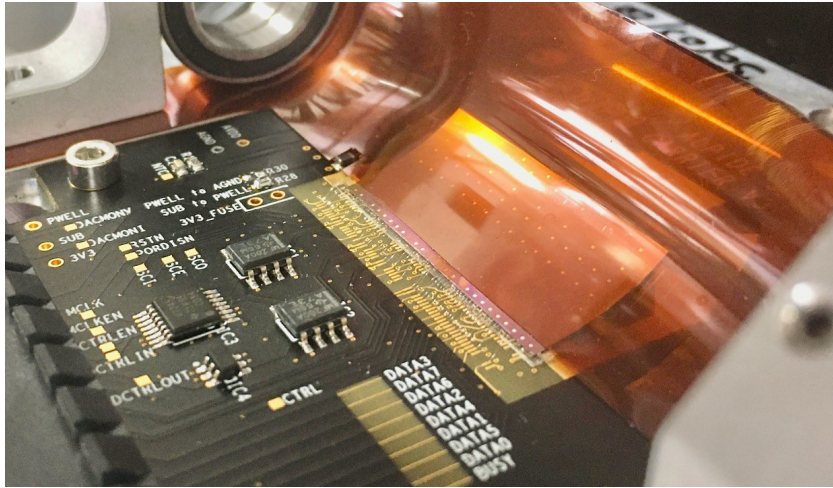
From now to ~next year

- ▶ Feasibility tests - **Done**
 - First tests in spring last year, next beam tests in July @SPS
- ▶ Test of chips bent in various directions - **Mostly done**
 - Lab and beam tests with wire bonded chips - **done**
 - SpTab bonded chips bent in lab - **ongoing**
 - μ ITS3 (6 bent chips, various radii) – **partially done**
- ▶ Test bent ALPIDE-Superchips - **ongoing**
 - Diced portions of wafers containing many ALPIDE reticles
 - Connection to existing test system & powering scheme **being produced**

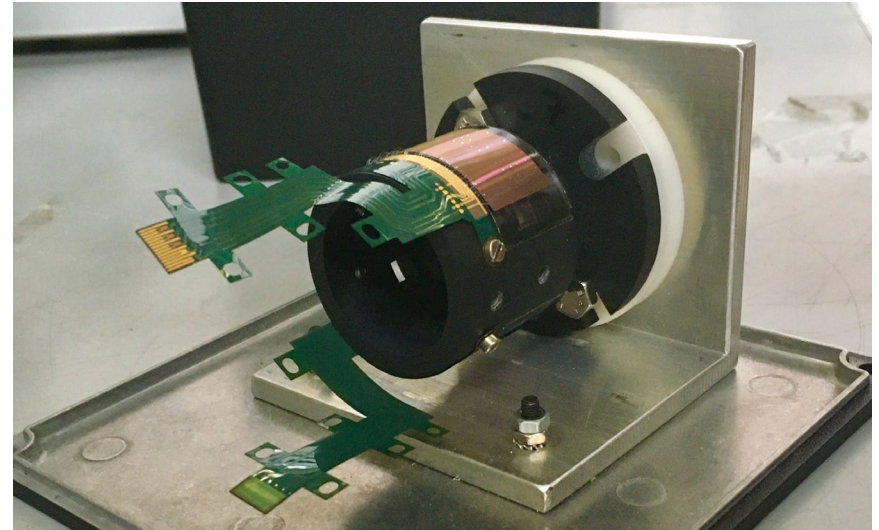


2020 Testbeams

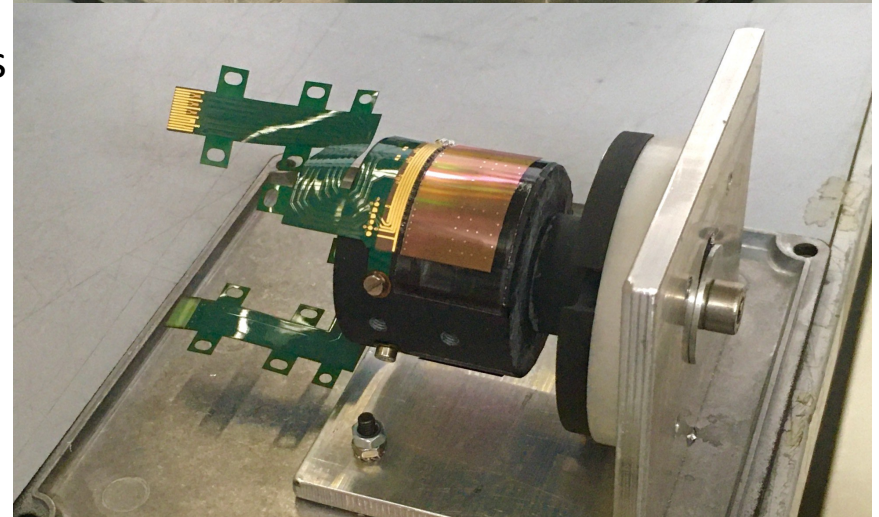
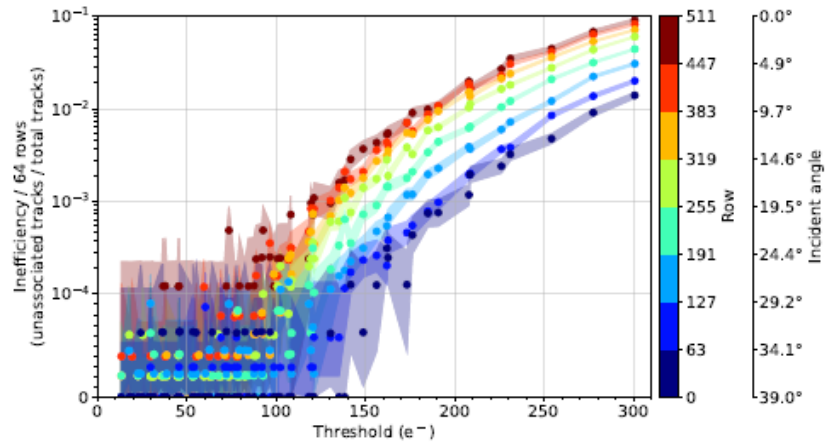
Bent ALPIDE
(short side)
18-22 mm radius



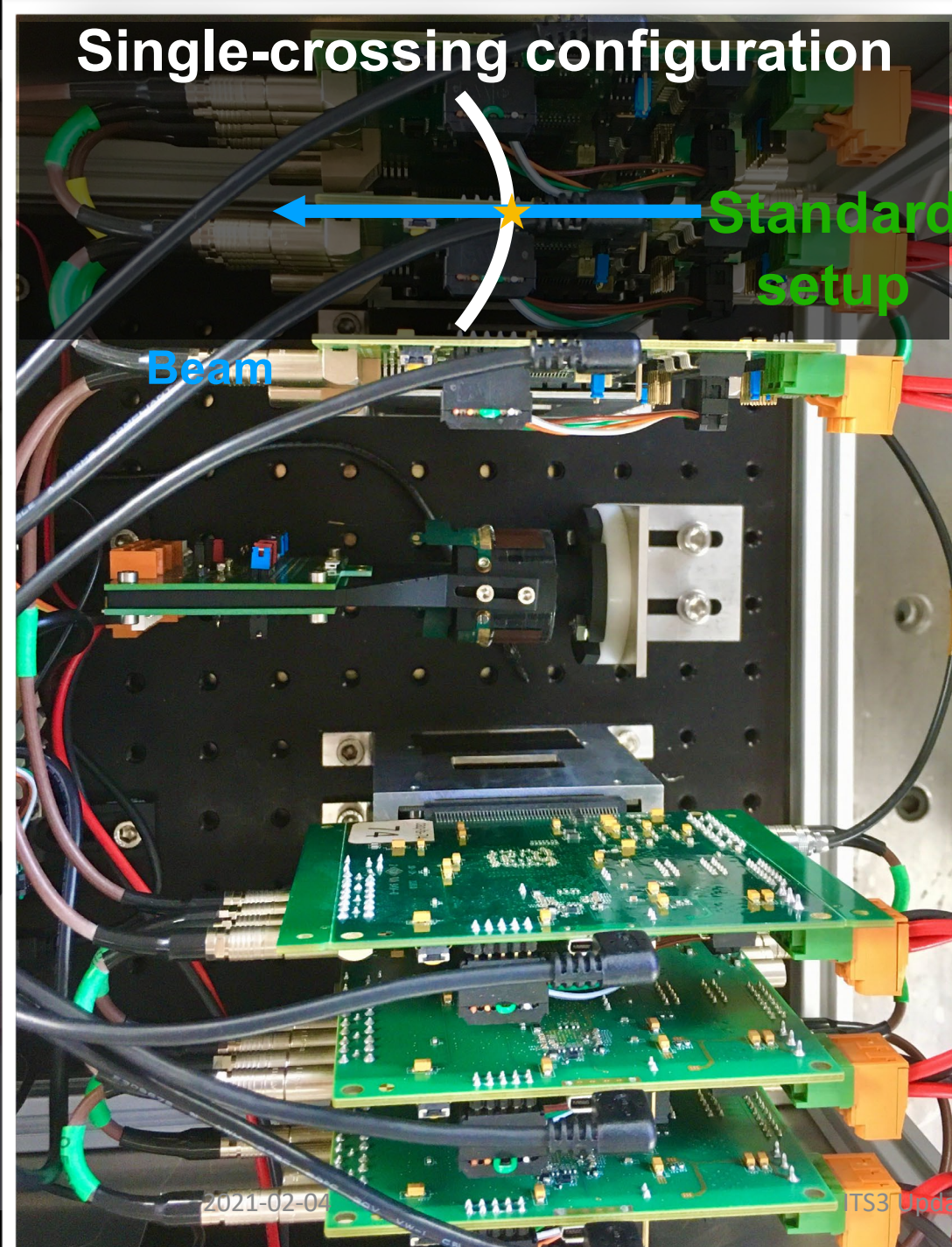
Bent ALPIDE
(long side)
18 mm radius



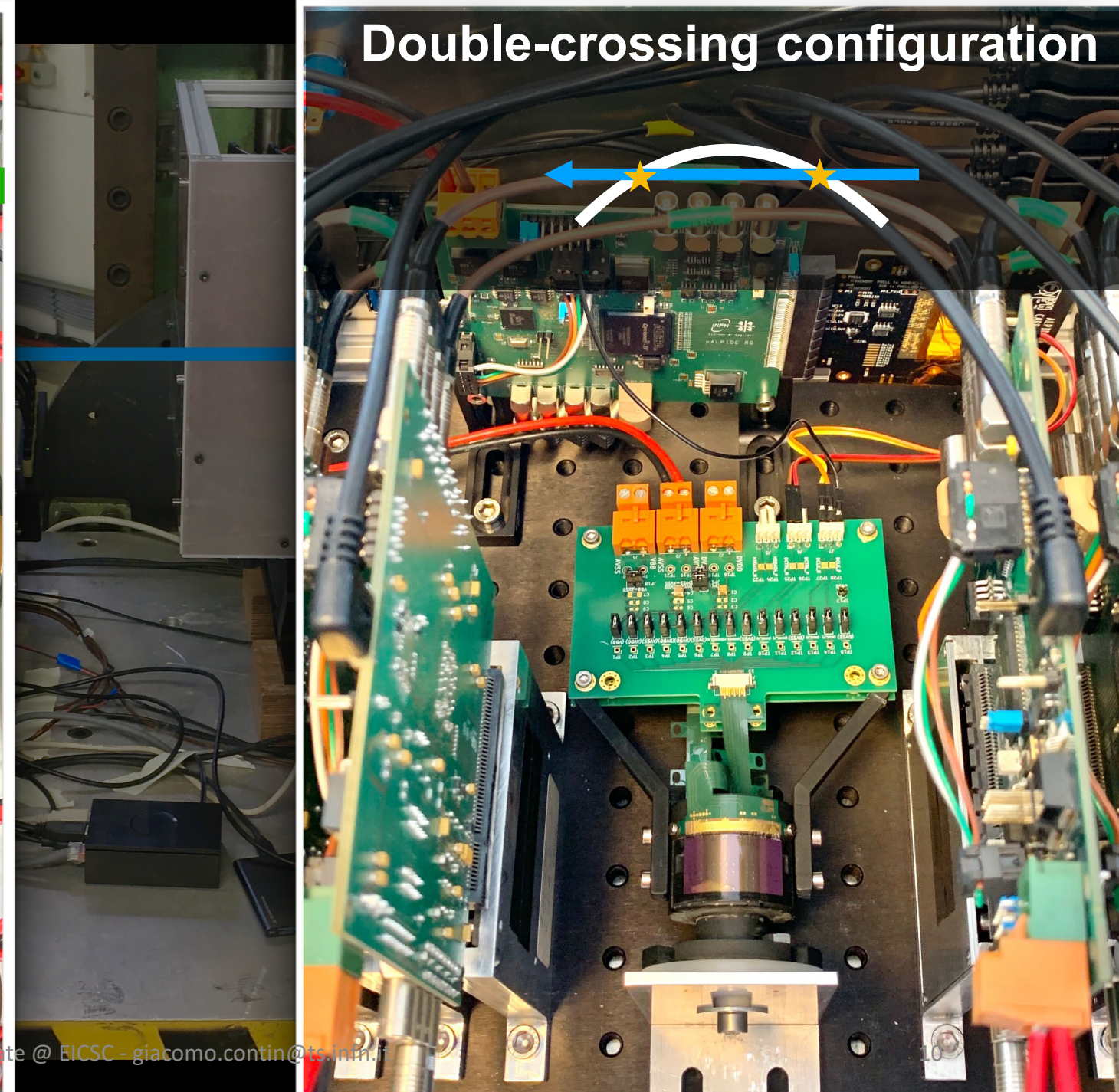
Measured inefficiency Vs Threshold (and Row)



Single-crossing configuration



Double-crossing configuration



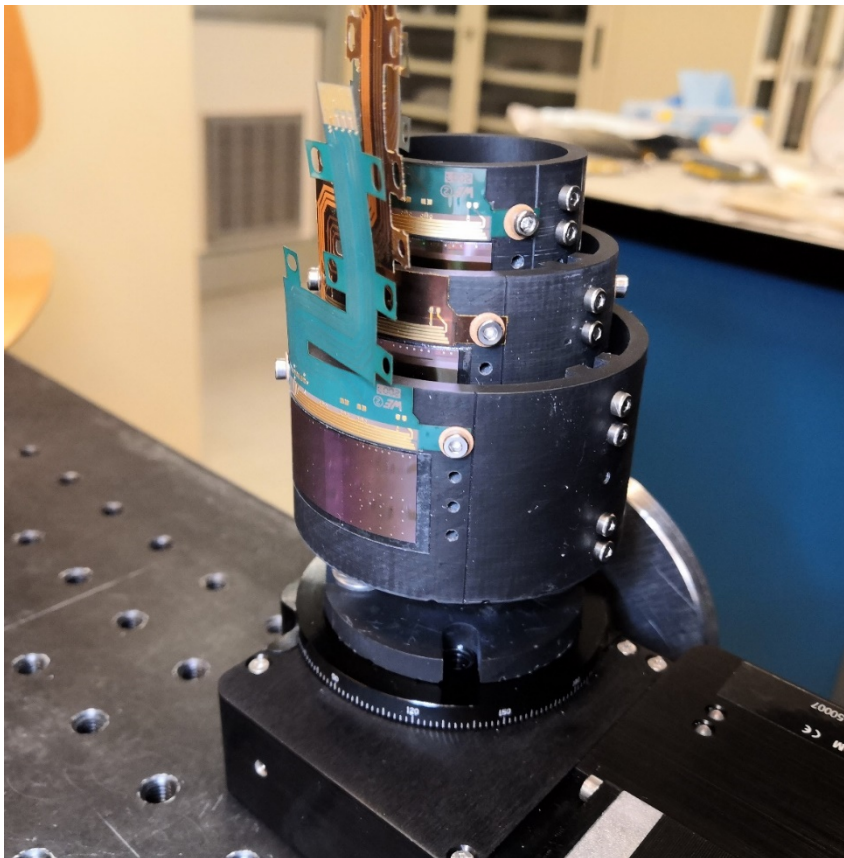
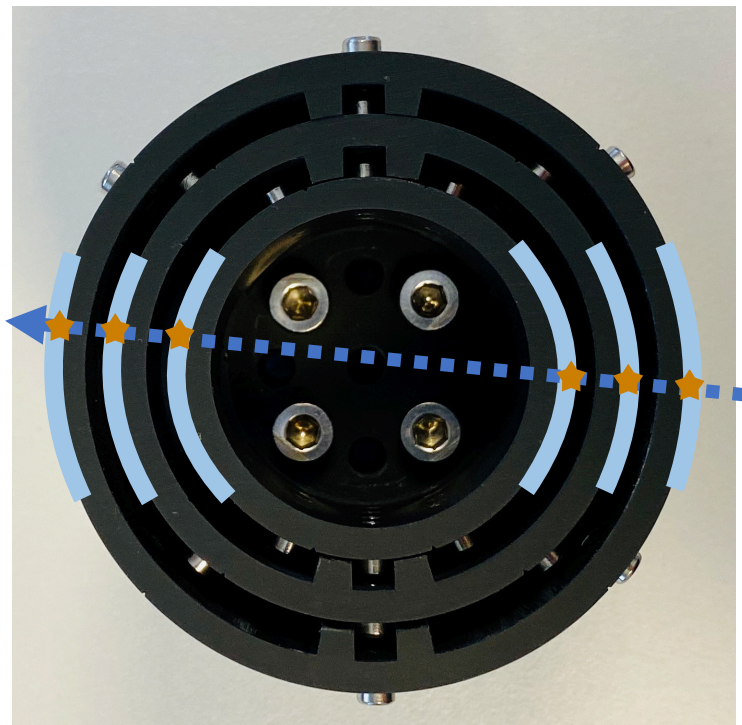
2021-02-04

TS3 Update @ EICSC - giacomo.contin@ts.infn.it

10

April 2021 Testbeam: 3-layer micro-ITS3

- Chips exposed for visibility

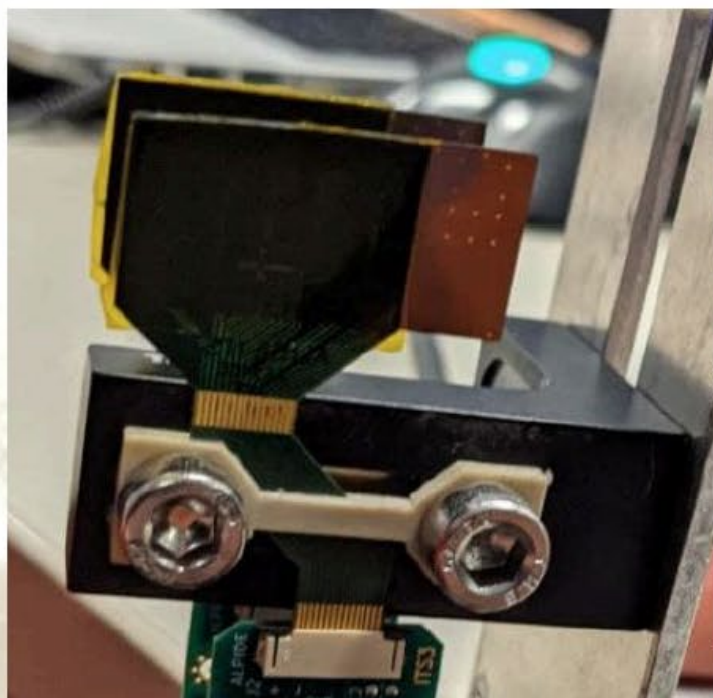
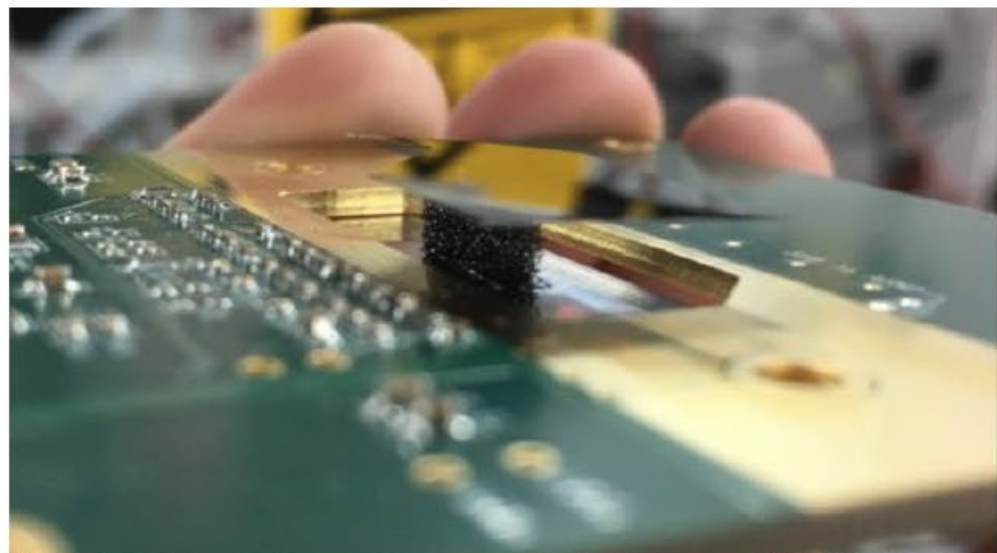


Goals

Lukas Lautner @ ITS3 WP3 04.05.2021

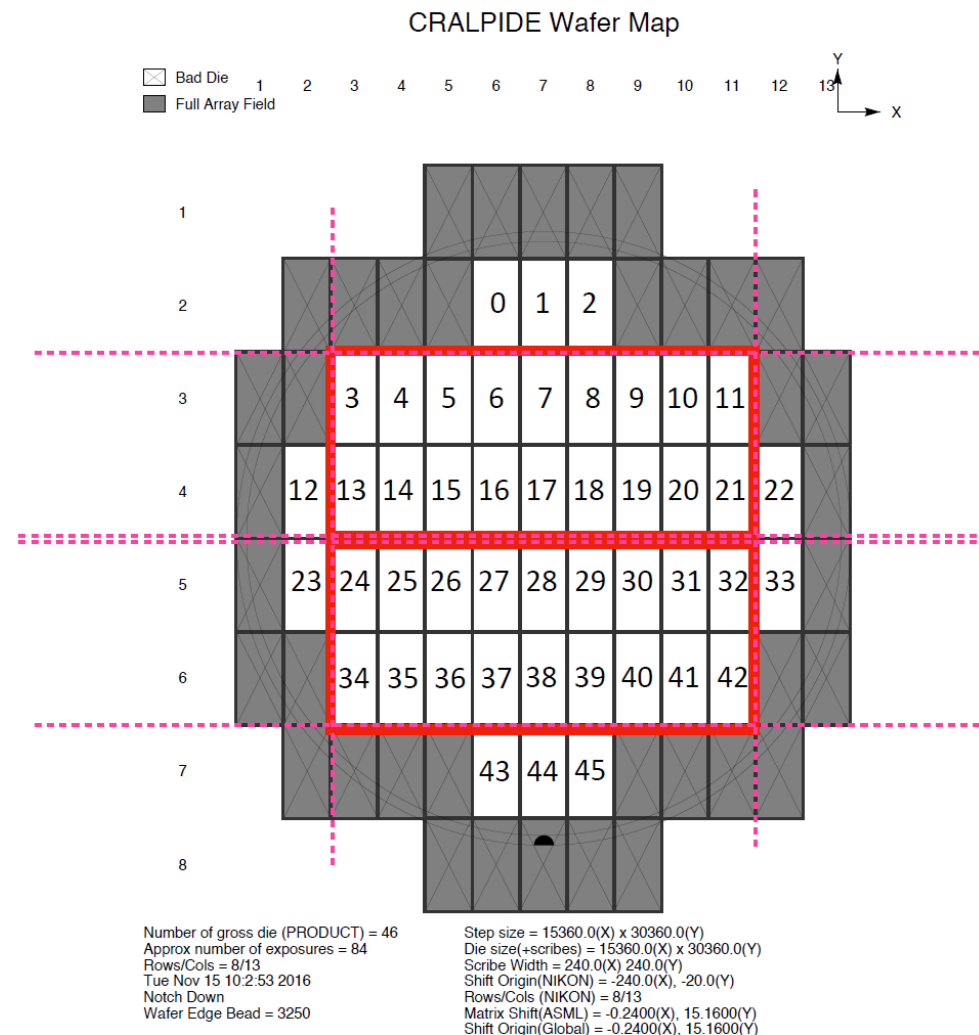
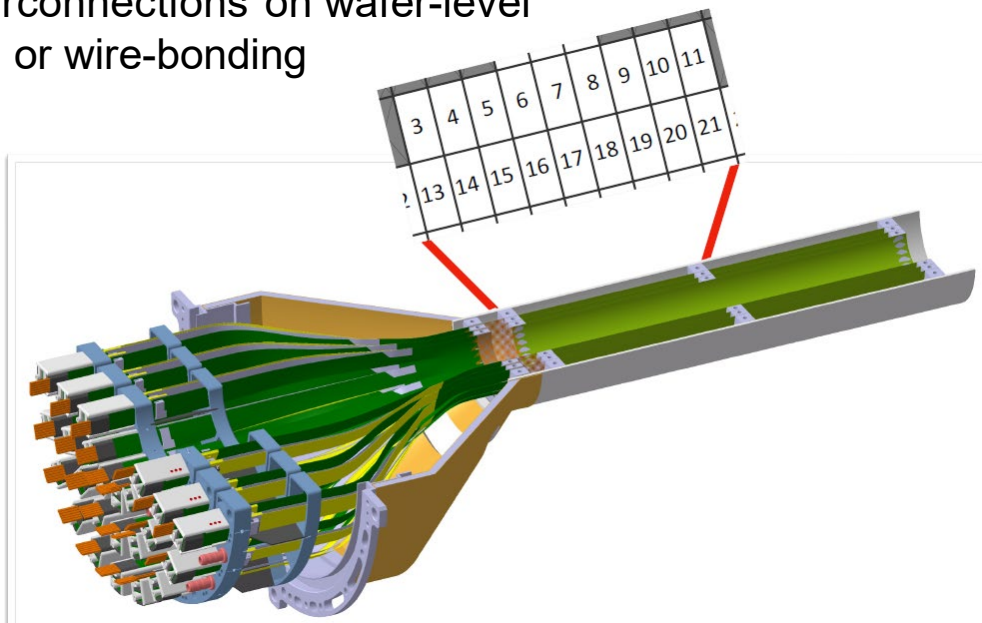


- 3 ALPIDE telescope
 - μ ITS3 (4 layers: L0B, L0T, L1T, L2T)
 - carbon foam
 - normal bent setup / parallel ALPIDE / ACF



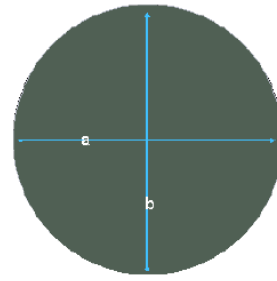
Moving to larger size: ALPIDE Super-chip

- Idea: cut out large “super chips” from a wafer
- about the area of 1/2 ITS3 half-layer 0
 - ~140 x 60 mm
- 9 x 2 chips
 - 9 interconnection areas in z-direction
- need individual connections:
 - no interconnections on wafer-level
 - SpTAB or wire-bonding

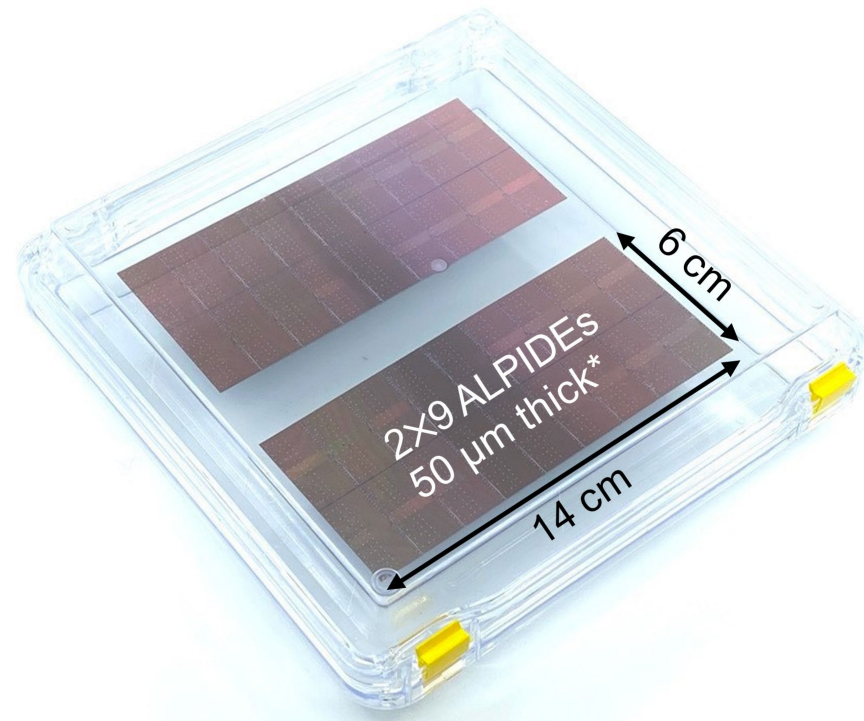
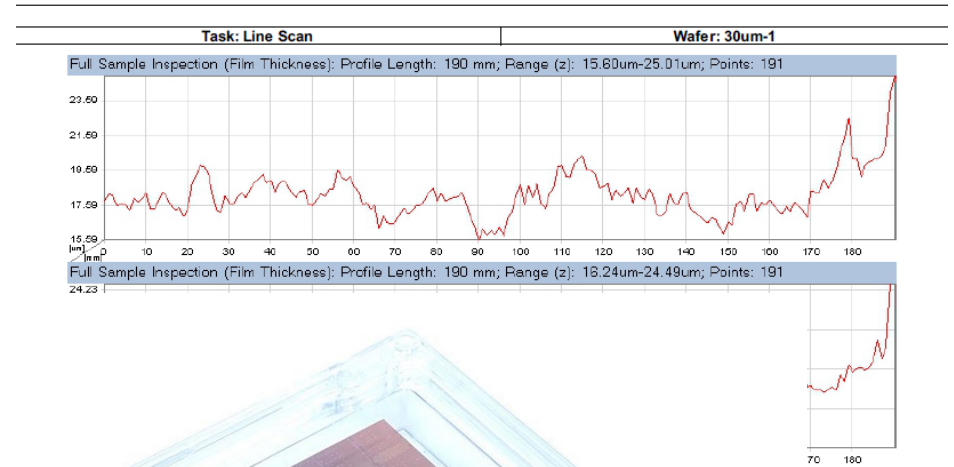


Super-ALPIDE project

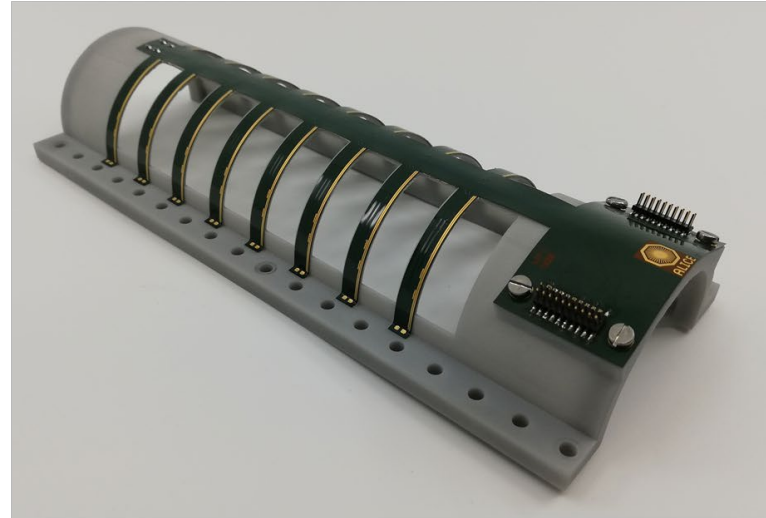
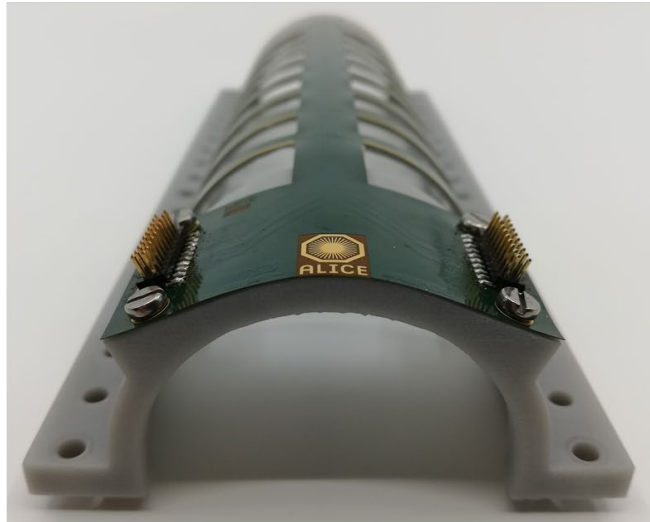
- Thinning and dicing
 - 30 – 40 – 50 μm / 9*2 ALPIDE matrix
 - 30 μm example, as measured by the thinning company through optical scan
 - 18.6 μm average with 1.4 μm st. dev
 - Does not include ~ 11 μm thick metal stack
- Shipping membrane box for large size dice
 - Larger size needed for final size
 - To be optimized and validated



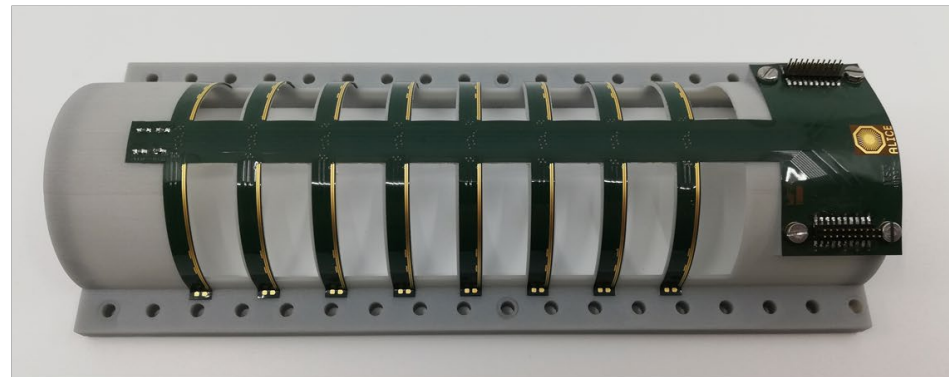
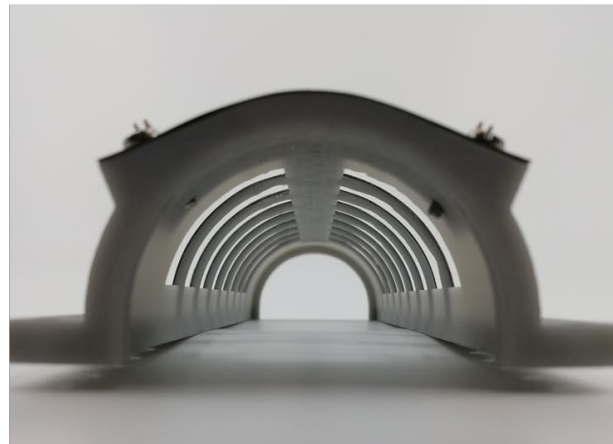
M. Mager @ ITS3 WP4



Super-ALPIDE project: FPC + Exoskeleton

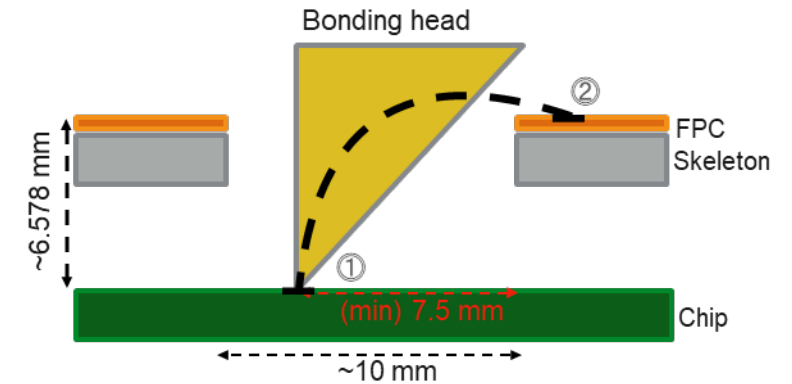


Dimensions, tolerance,
details being optimized

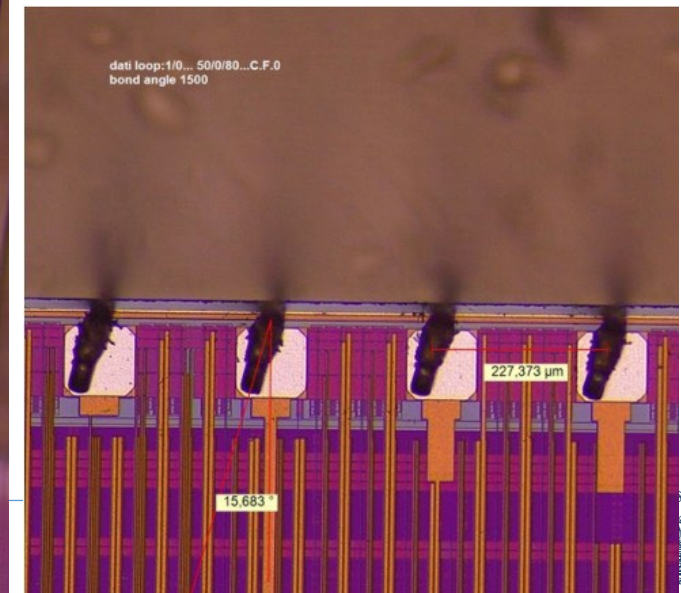
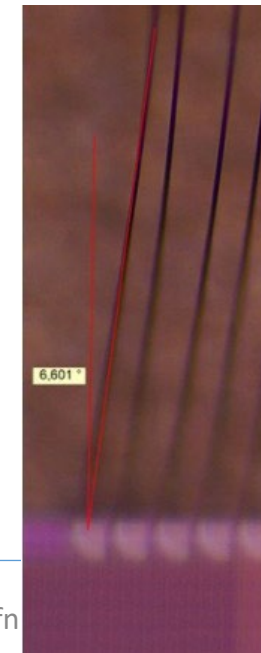
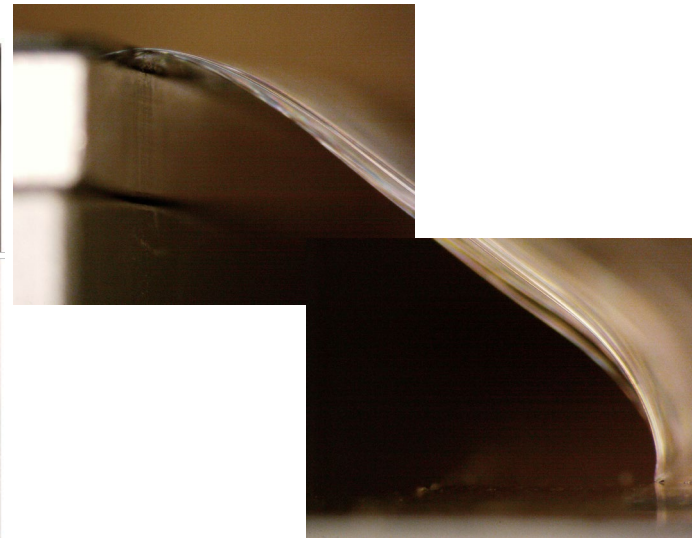
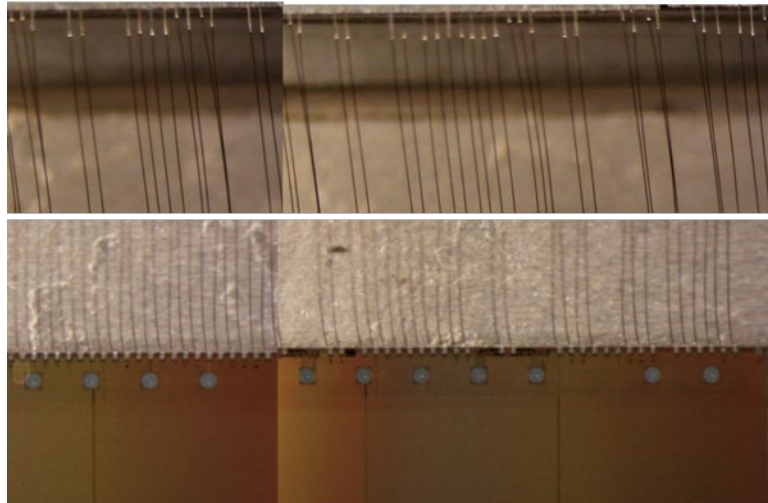


Super-ALPIDE: wire-bonding @ Bari

- Preliminary wire-bonding test on real ALPIDE, avoiding conflict between bonding head and FPC
 - Loop height: 6.6mm (target: ~ 8mm)
 - Distance between pads along z: 8.7mm
 - First soldering on chip (down), second on FPC (up)
 - Inter-pad bondable distance $220\ \mu\text{m}$ = two consecutive small pads
 - 6 degrees angle between bonding pads direction and wire
 - Interference with previously soldered wires due to clamp dimensions
→ reduced by rotating the foot at chip pads by 15 degrees

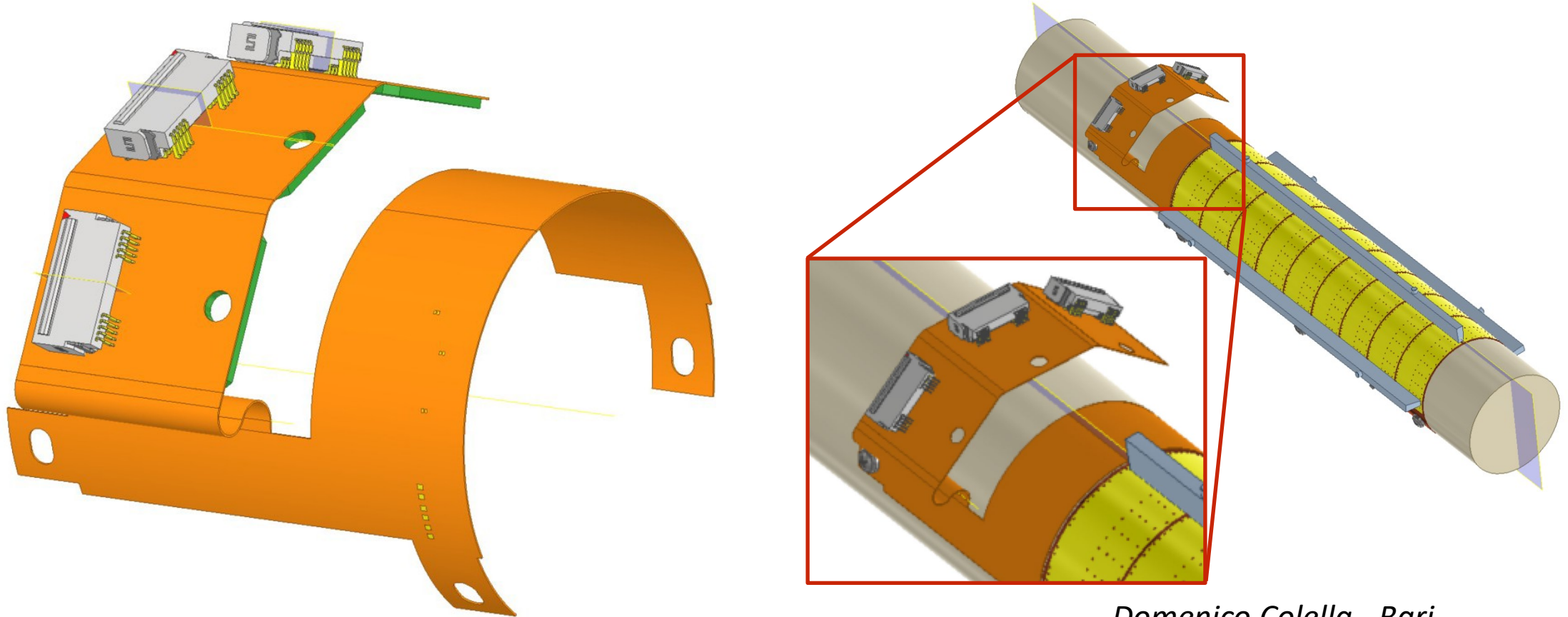


Domenico Colella - Bari



Super-ALPIDE Edge-FPC @ Bari

- First prototype of the final front-edge ITS3 interconnections

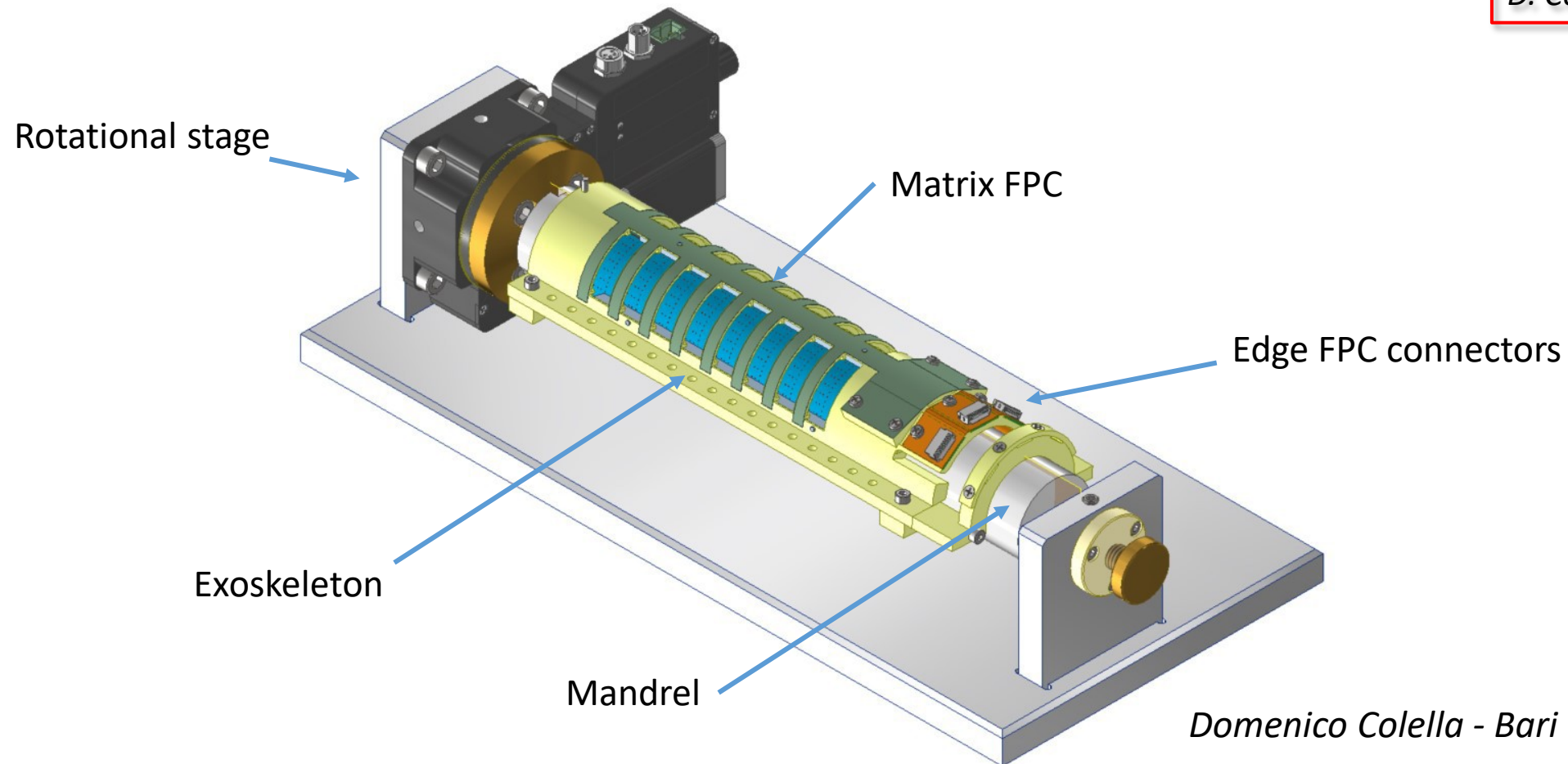


Domenico Colella - Bari

Super-ALPIDE wire-bonding setup @ Bari

- Component design being finalized or already in production

D. Colella @ ITS3 WP4

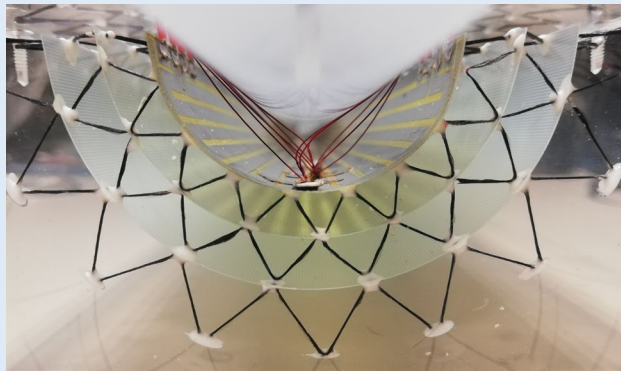
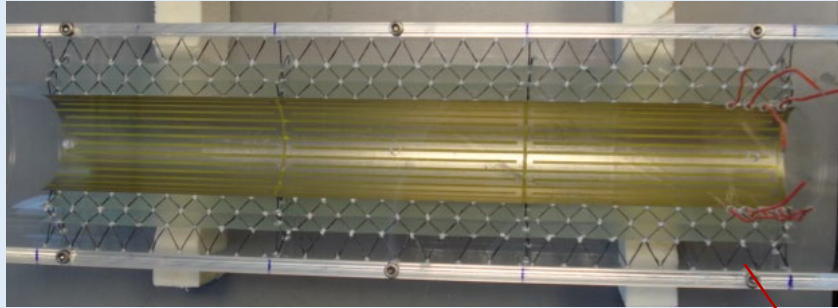




BBM1 DONE

L0= heater; L1= G10 sheet; L2=G10 sheet

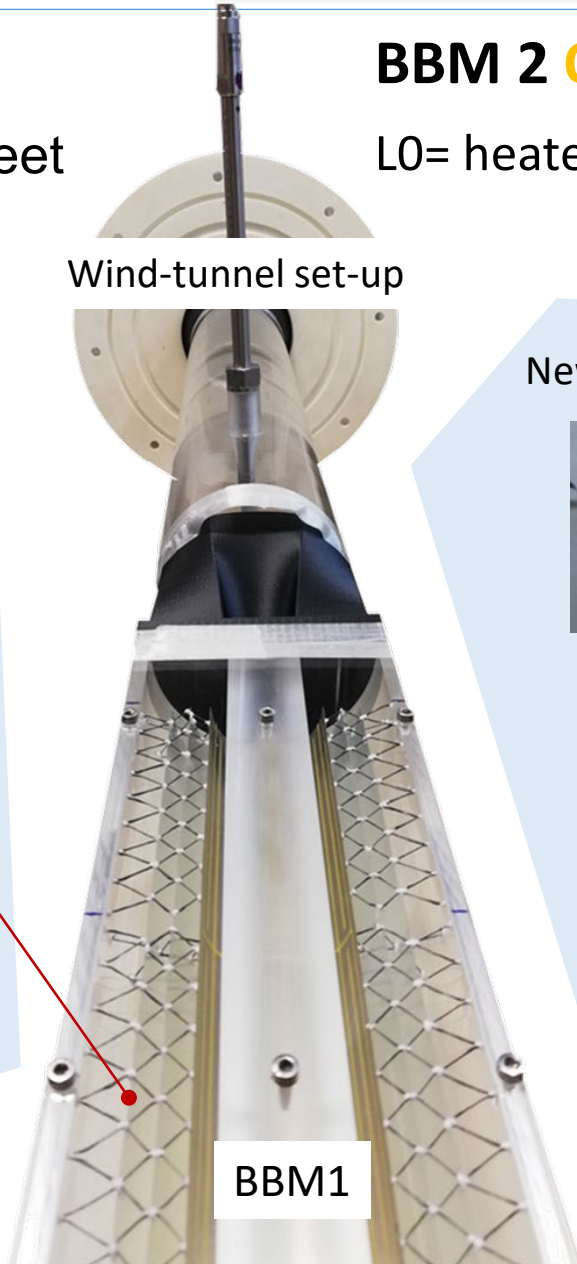
3 dummy layers (fiberglass),
first equipped with kapton heaters



BBM 2 ONGOING

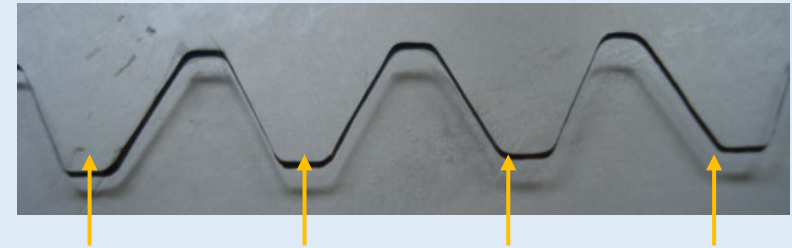
L0= heater; L1= heater; L2= heater

Wind-tunnel set-up



BBM1

New CFRP support design for BBM2 (Plan B for EM)



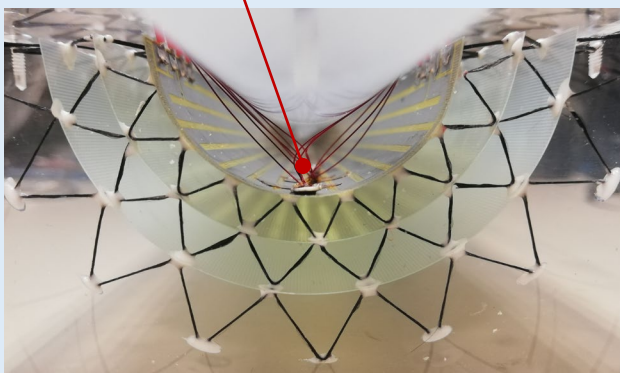
- Flat edges to minimize glue but have a reasonable gluing area.
- Cross section 1x0.05 mm²





BBM1 Ready for preliminary Test in wind tunnel

L0 equipped with 3 PT1000 temperature sensors.



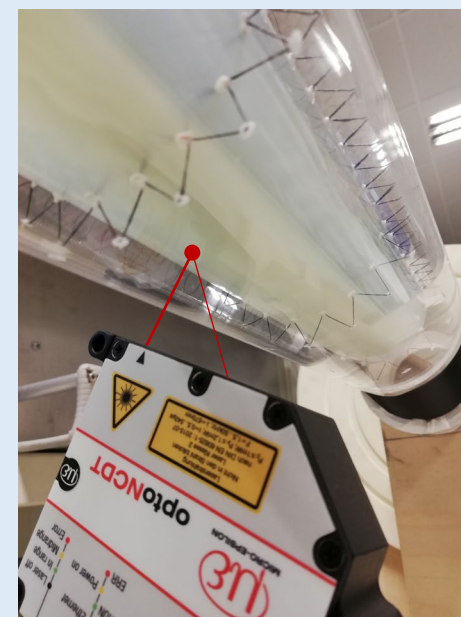
Wind-tunnel set-up



BBM1

Next implementation of ..

Laser displacement sensor
Micro-Epsilon ILD2300-20LL
Resolution 0.3micron

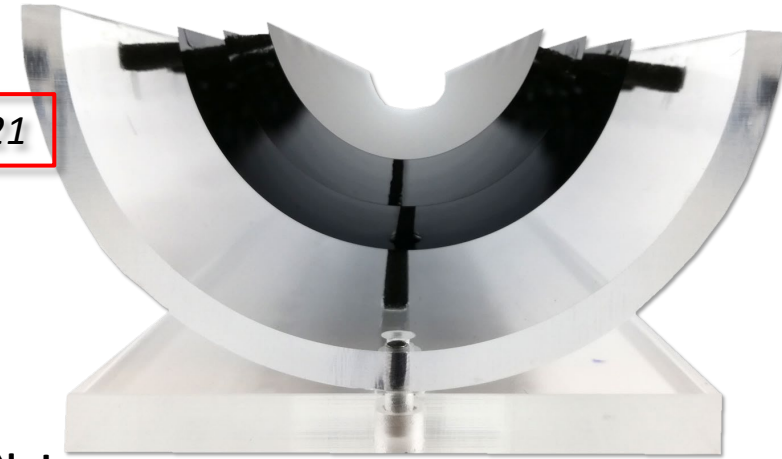


Highlights: Engineering model 1 --> Fully assembled

The first half barrel model with dummy silicon HLS at nominal radius has been completed.

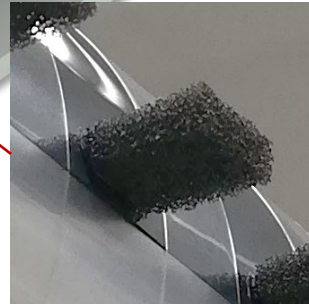
Items	Th. [um]	L [mm]	Circ. [mm]
L0	50	280	56.5
L1	40	280	74.4
L2	40	280	93.2

C. Gargiulo / M. Angeletti @ ITS3 Plenary 23.04.2021



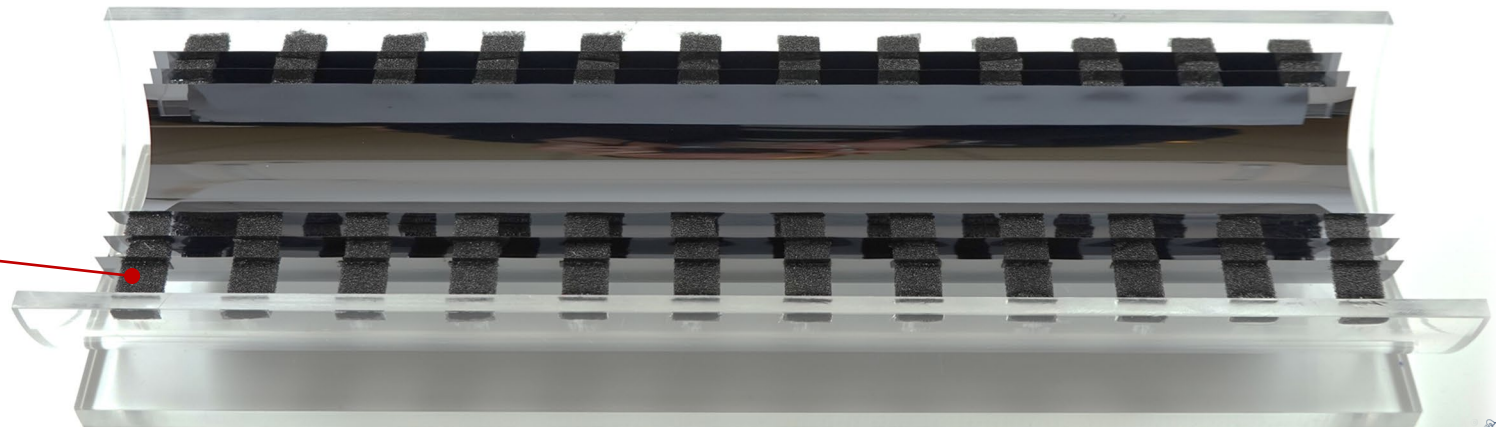
Notes:

- Layers' position guaranteed by small foam wedges only;
- 50μm thick L0 has been used to demonstrate bendability (min radius)

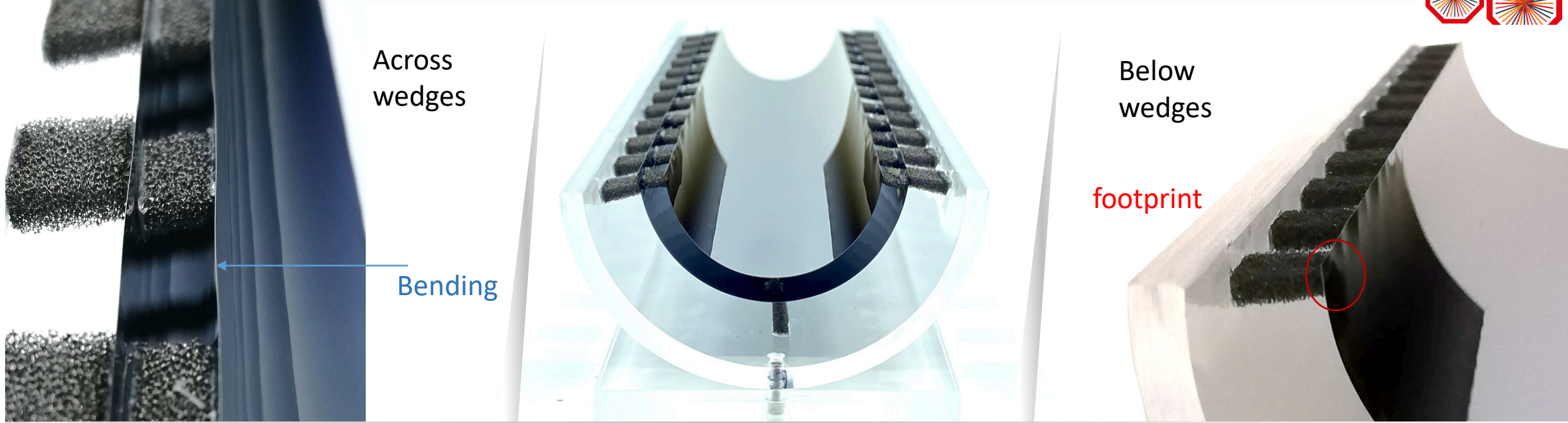


@Duocell ERG wedge

@CERN



EM1: Improvement of sensor interface to support



C. Gargiulo / M. Angeletti @ ITS3 Plenary 23.04.2021

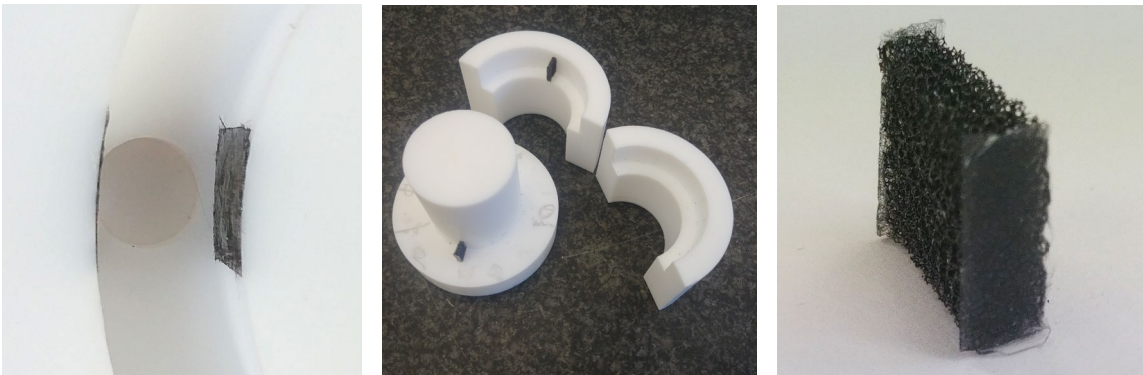
@CERN

ongoing

MINIMIZE footprint → special preparation of carbon foam/fleece (also to reduce glue)

MINIMIZE bending → enlarge contact surface i.e. increase number of wedges; continuous wedge (requires vacuum chuck).

Hybrid solution with Al porous vacuum chuck and thin FINGER-maylar foil under investigation



Possible engagements in ITS3 WPs towards EIC dev.

- MLR1 test structure and small matrix characterization
 - Test setup development and sensor characterization for EIC
- Large sensor thinning/bending/interconnections
 - Development for EIC vertex radii/dimensions
- Mechanics and cooling development
 - Development for EIC vertex radii/dimensions
 - Integration with EIC services